



Description

The SH8K3TB1 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 30V$ $I_D = 8A$

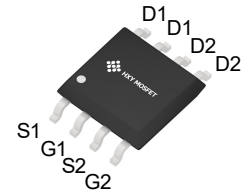
$R_{DS(ON)} < 19m\Omega$ @ $V_{GS}=4.5V$

Application

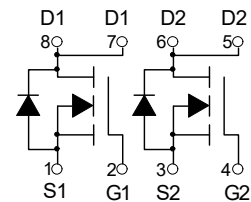
Battery protection

Load switch

Uninterruptible power supply



SOP-8



Dual N-Channel MOSFET

Ordering Information

Product ID	Pack	Brand	Qty(PCS)
SH8K3TB1	SOP-8	HXY MOSFET	3000

Absolute Maximum Ratings@ $T_j=25^\circ C$ (unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_A=25^\circ C$	Drain Current, $V_{GS} @ 4.5V^3$	8	A
$I_D@T_A=70^\circ C$	Drain Current, $V_{GS} @ 4.5V^3$	5.8	A
I_{DM}	Pulsed Drain Current ¹	37	A
$P_D@T_A=25^\circ C$	Total Power Dissipation	1.5	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
R_{thj-a}	Maximum Thermal Resistance, Junction-ambient ³	85	$^\circ C/W$



Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	---	---	V
ΔBV _{DSS} /ΔT	BVDSS Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.034	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =7A	---	17	19	mΩ
		V _{GS} =4.5V, I _D =4A	---	22	28	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.2	---	2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-5.8	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =24V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =24V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =7A	---	6	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	2.5	---	Ω
Q _g	Total Gate Charge (4.5V)	V _{DS} =15V, V _{GS} =4.5V, I _D =7A	---	6	---	nC
Q _{gs}	Gate-Source Charge		---	2.5	---	
Q _{gd}	Gate-Drain Charge		---	2.1	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =15V, V _{GS} =10V, R _G =3.3Ω I _D =7A	---	2.4	---	ns
T _r	Rise Time		---	7.8	---	
T _{d(off)}	Turn-Off Delay Time		---	22	---	
T _f	Fall Time		---	4	---	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	572	---	pF
C _{oss}	Output Capacitance		---	80	---	
C _{rss}	Reverse Transfer Capacitance		---	65	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V, Force Current	---	---	7.3	A
I _{SM}	Pulsed Source Current ^{2,5}		---	---	37	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V
t _{rr}	Reverse Recovery Time	I _F =7A, dI/dt=100A/μs, T _J =25°C	---	20	---	nS
Q _{rr}	Reverse Recovery Charge		---	1.1	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The EAS data shows Max. rating. The test condition is V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=21A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.



Typical Characteristics



Fig.1 Typical Output Characteristics

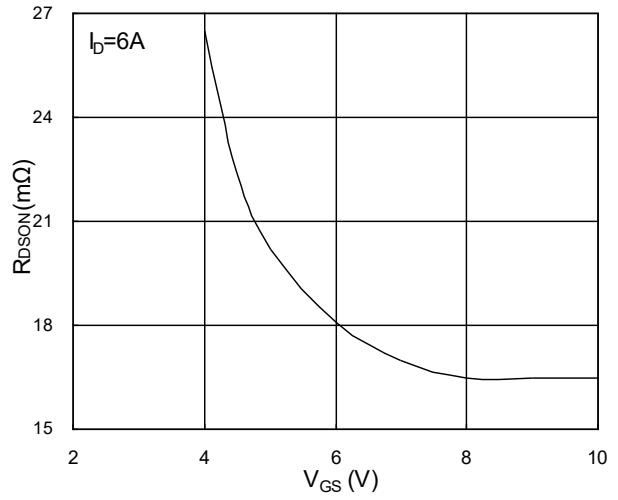


Fig.2 On-Resistance vs. G-S Voltage

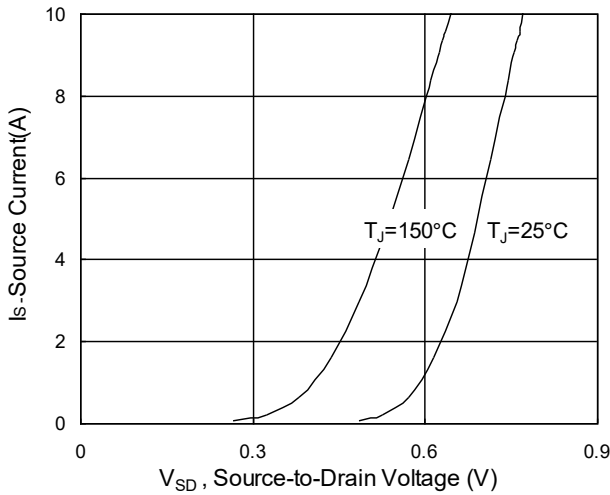


Fig.3 Forward Characteristics Of Reverse

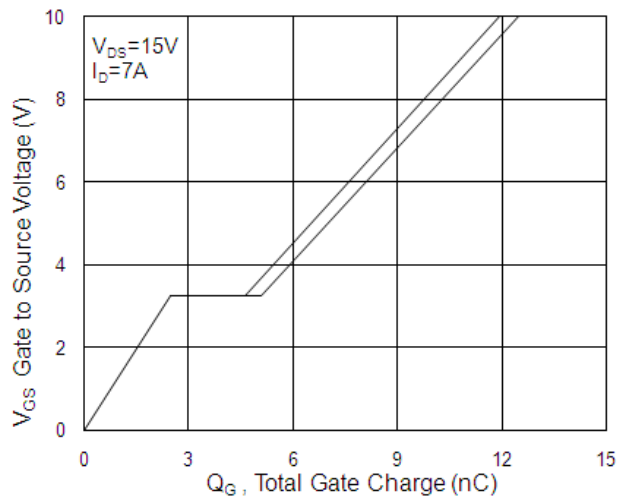


Fig.4 Gate-Charge Characteristics

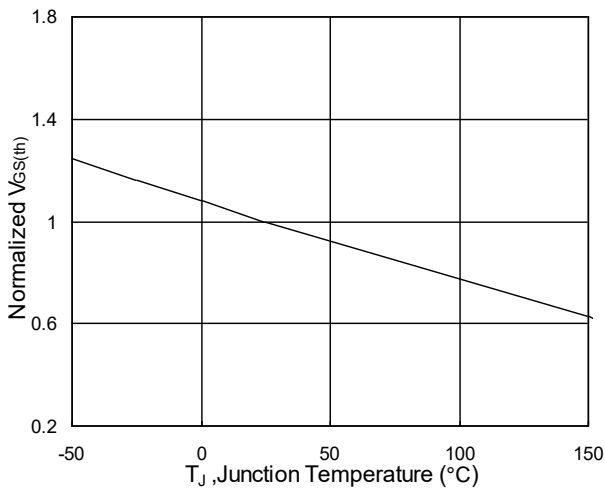


Fig.5 Normalized V_{GS(th)} vs. T_J

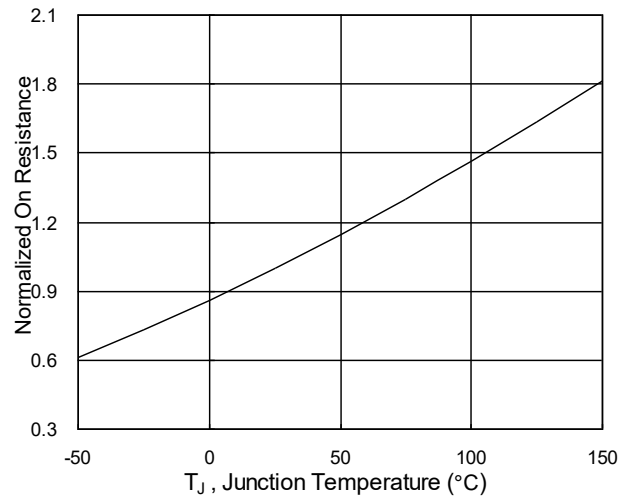


Fig.6 Normalized R_{DS(on)} vs. T_J

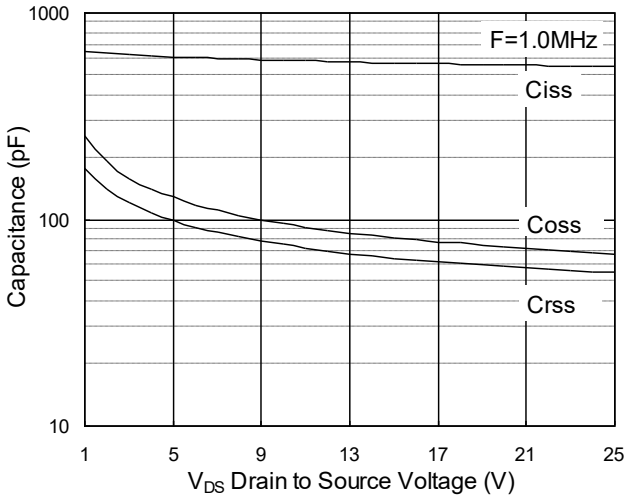


Fig.7 Capacitance

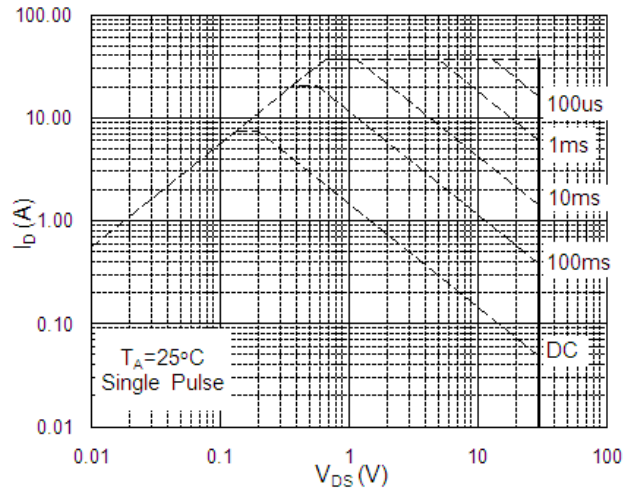


Fig.8 Safe Operating Area

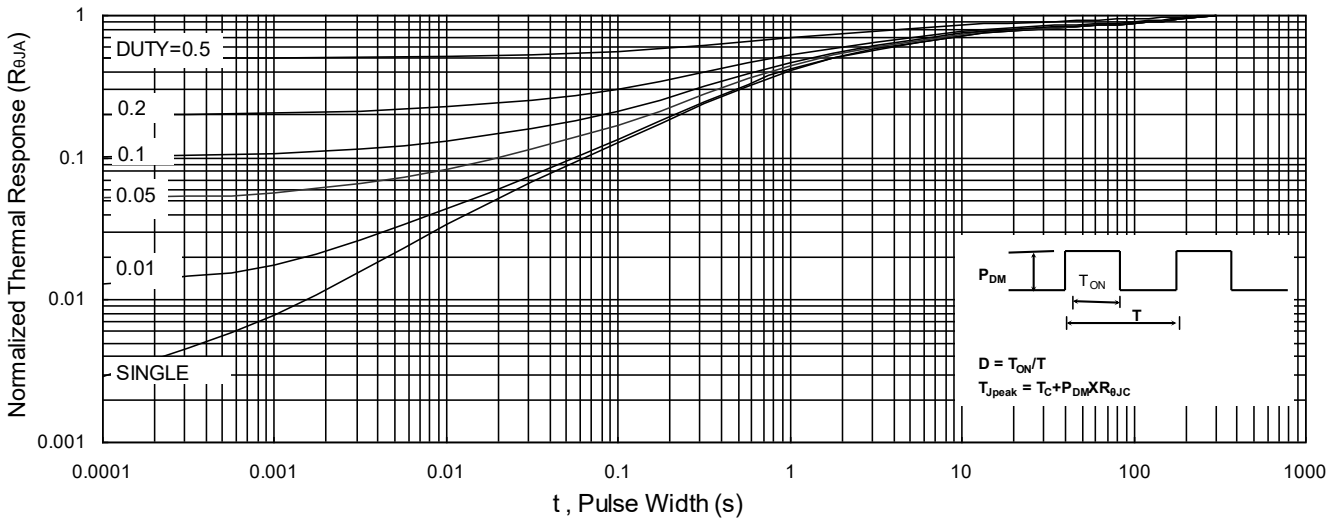


Fig.9 Normalized Maximum Transient Thermal Impedance

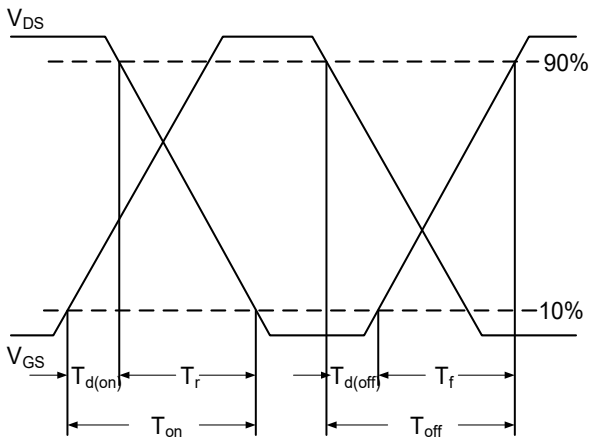


Fig.10 Switching Time Waveform

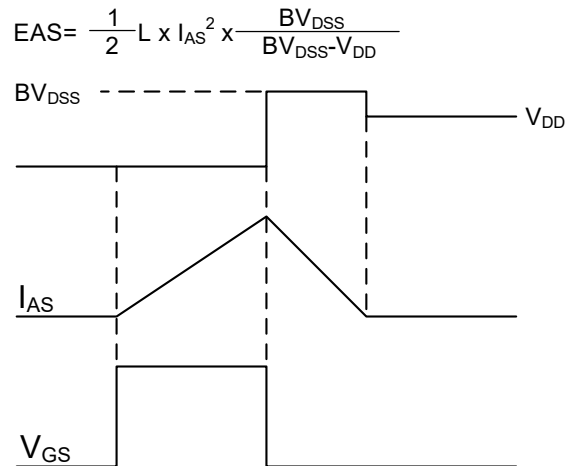


Fig.11 Unclamped Inductive Switching Waveform



SOP-8 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
theta	0°	8°	0°	8°



Note:
1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.



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